

14N65-ML

Power MOSFET

14A, 650V N-CHANNEL POWER MOSFET

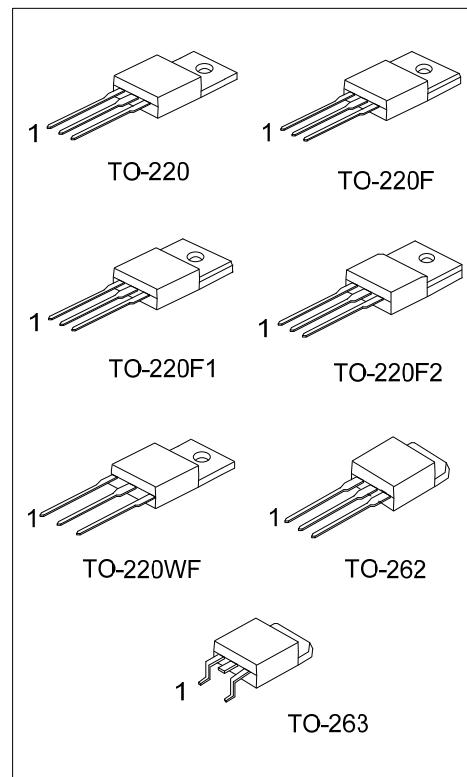
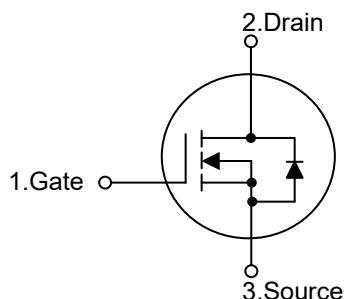
■ DESCRIPTION

The UTC 14N65-ML is a high voltage power MOSFET combines advanced planar MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

- * $R_{DS(ON)} \leq 0.65 \Omega$ @ $V_{GS}=10V$, $I_D=7.0A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

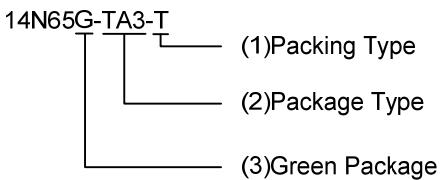
■ SYMBOL



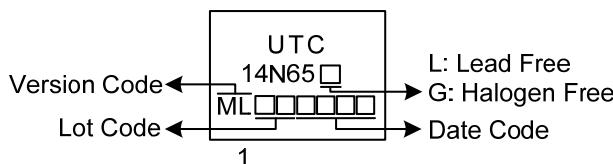
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
14N65L-TA3-T	14N65G-TA3-T	TO-220	G	D	S	Tube
14N65L-TF1-T	14N65G-TF1-T	TO-220F1	G	D	S	Tube
14N65L-TF2-T	14N65G-TF2-T	TO-220F2	G	D	S	Tube
14N65L-TF3-T	14N65G-TF3-T	TO-220F	G	D	S	Tube
14N65L-TW1-T	14N65G-TW1-T	TO-220WF	G	D	S	Tube
14N65L-T2Q-T	14N65G-T2Q-T	TO-262	G	D	S	Tube
14N65L-TQ2-T	14N65G-TQ2-T	TO-263	G	D	S	Tube
14N65L-TQ2-R	14N65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

 14N65G-TA3-T	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, TW1: TO-220WF, T2Q: TO-262, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
---	--

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	14	A
Pulsed Drain Current (Note 2)		I_{DM}	28	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	800	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.7	V/ns
Power Dissipation	TO-220/TO-262/TO-263	P_D	235	W
	TO-220F/TO-220F1		52	W
	TO-220F2/TO-220WF			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30\text{mH}$, $I_{AS} = 7.3\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 14\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C/W}$
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	0.53	$^\circ\text{C/W}$
	TO-220F/TO-220F1			
	TO-220F2/TO-220WF		2.4	$^\circ\text{C/W}$

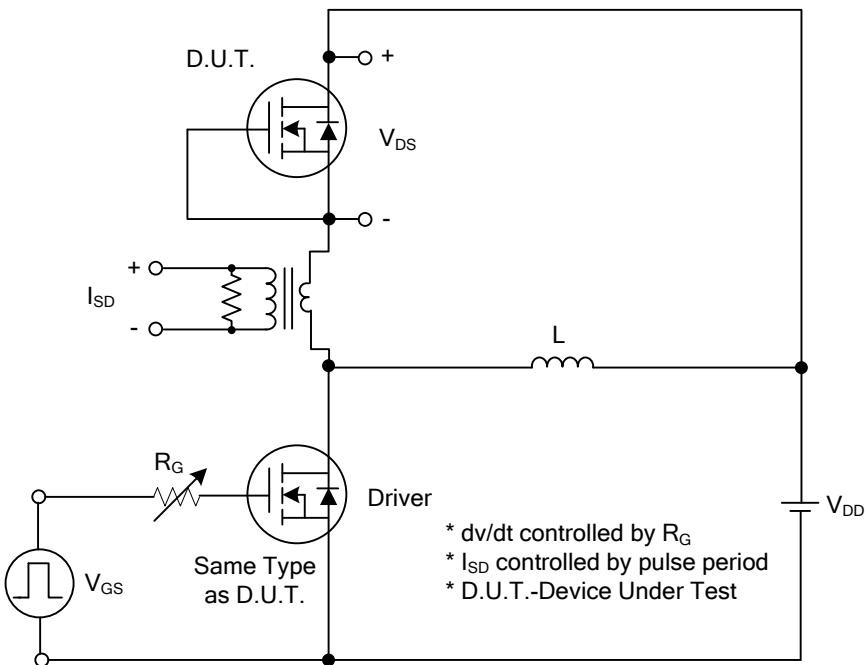
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$		10		μA
Gate- Source Leakage Current	Forward	$V_{\text{GS}}=30\text{V}, V_{\text{DS}}=0\text{V}$		100		nA
	Reverse	$V_{\text{GS}}=-30\text{V}, V_{\text{DS}}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=7.0\text{A}$		0.55	0.65	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$		1950		pF
Output Capacitance	C_{OSS}			180		pF
Reverse Transfer Capacitance	C_{RSS}			14		pF
Gate Resistance	R_{G}	$V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		3		Ω
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_{G}	$V_{\text{DS}}=520\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=14\text{A}$ $I_{\text{G}}=1\text{mA}$ (Note 1, 2)		44		nC
Gate-Source Charge	Q_{GS}			10		nC
Gate-Drain Charge	Q_{GD}			12		nC
Turn-On Delay Time (Note 1)	$t_{\text{D(ON)}}$	$V_{\text{DS}}=100\text{V}, V_{\text{GS}}=10\text{V}, I_{\text{D}}=14\text{A}$ $R_{\text{G}}=25\Omega$ (Note 1, 2)		28		ns
Turn-On Rise Time	t_{R}			24		ns
Turn-Off Delay Time	$t_{\text{D(OFF)}}$			150		ns
Turn-Off Fall Time	t_{F}			34		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Body-Diode Continuous Current	I_{s}				14	A
Maximum Body-Diode Pulsed Current	I_{SM}				28	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_{\text{s}}=14\text{A}, V_{\text{GS}}=0\text{V}$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_{\text{s}}=14\text{A}, V_{\text{GS}}=0\text{V}$ $di/dt=100\text{A}/\mu\text{s}$		430		ns
Reverse Recovery Charge	Q_{rr}			14		μC

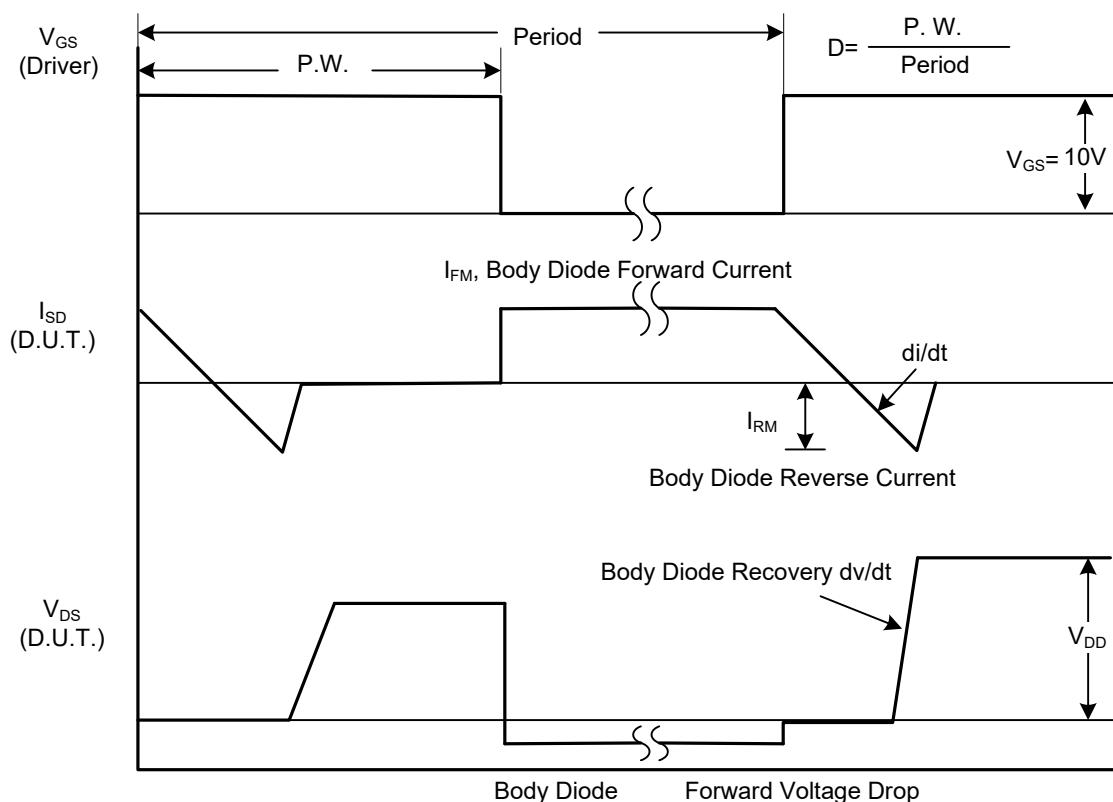
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

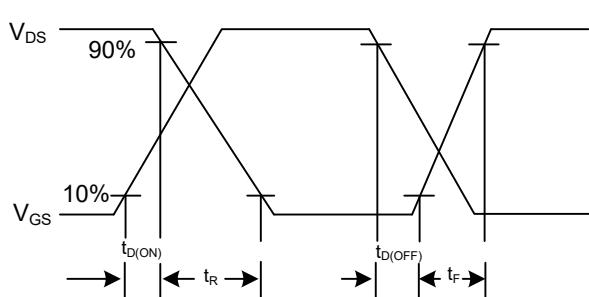
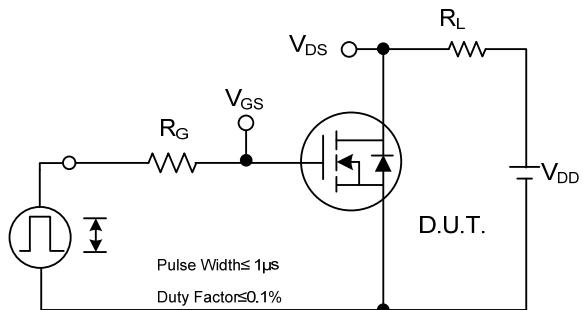


Peak Diode Recovery dv/dt Test Circuit



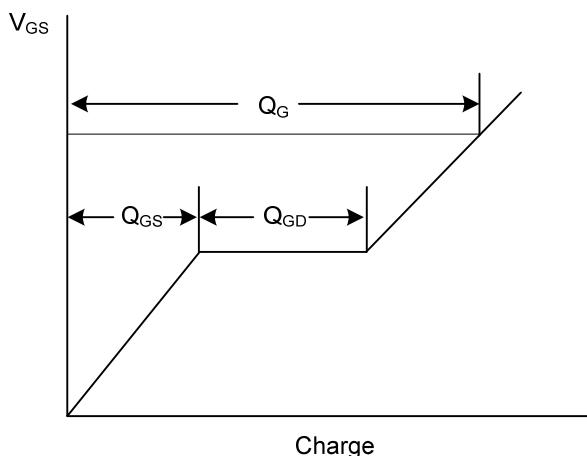
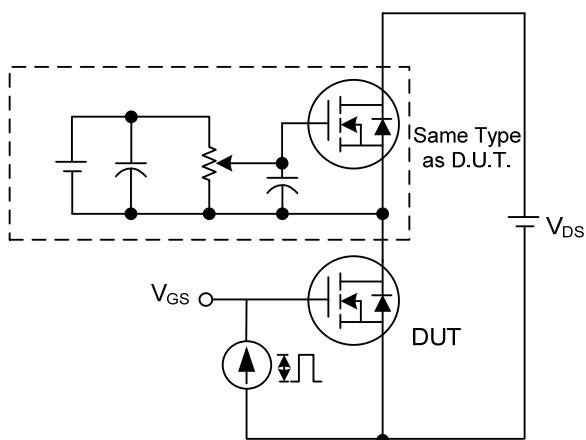
Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS



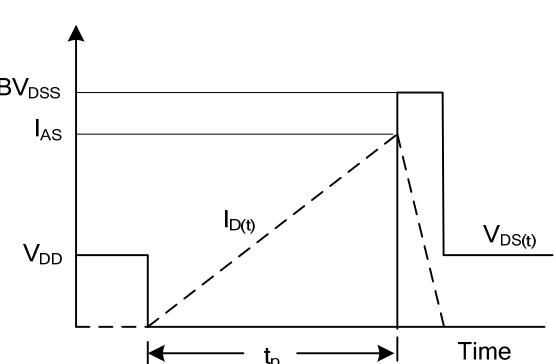
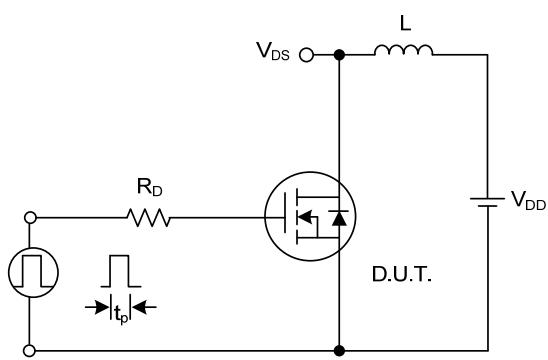
Switching Test Circuit

Switching Waveforms



Gate Charge Test Circuit

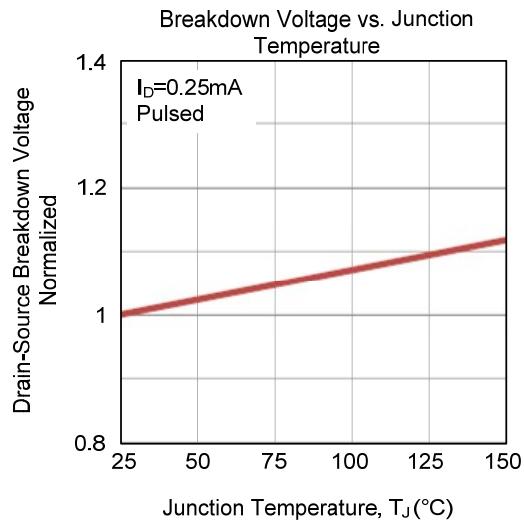
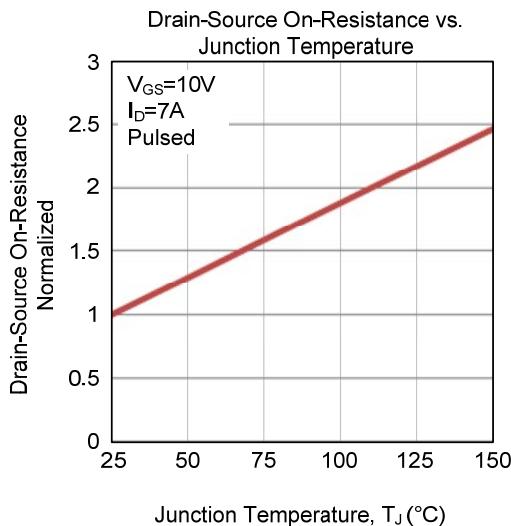
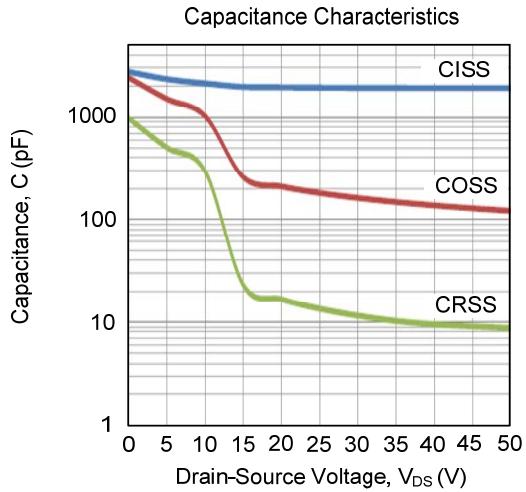
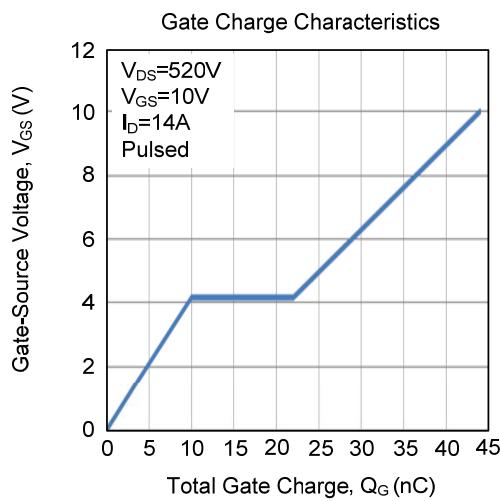
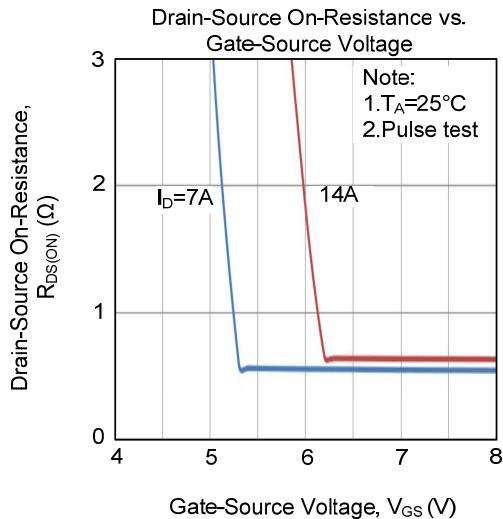
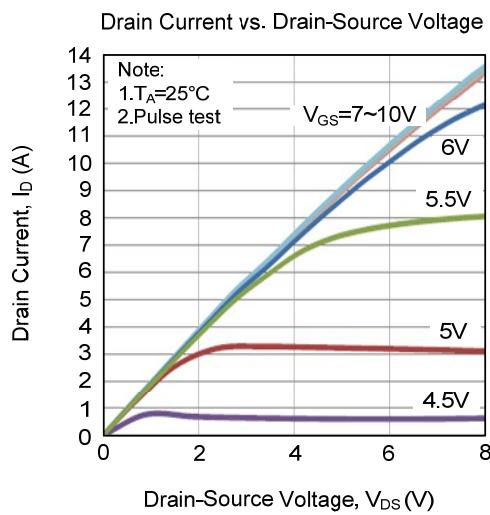
Gate Charge Waveform



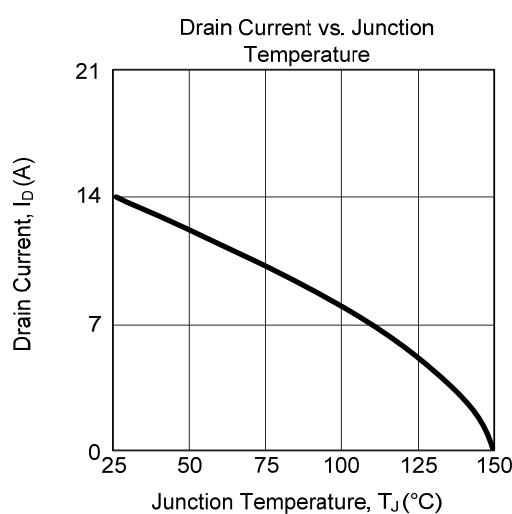
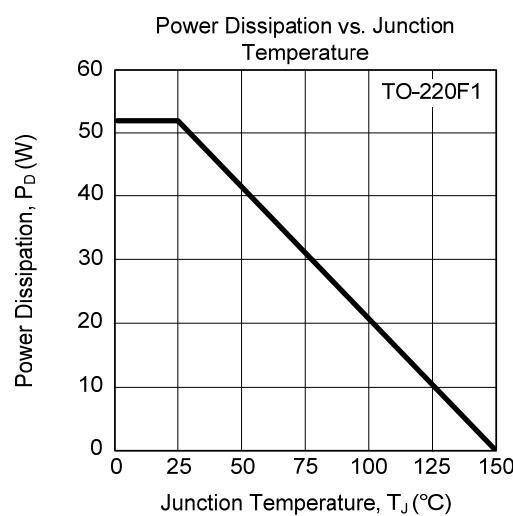
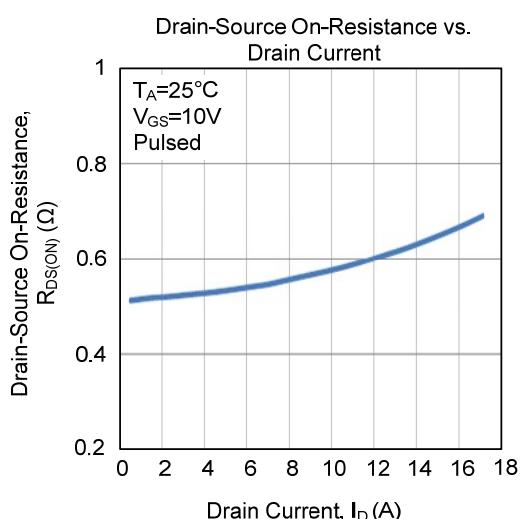
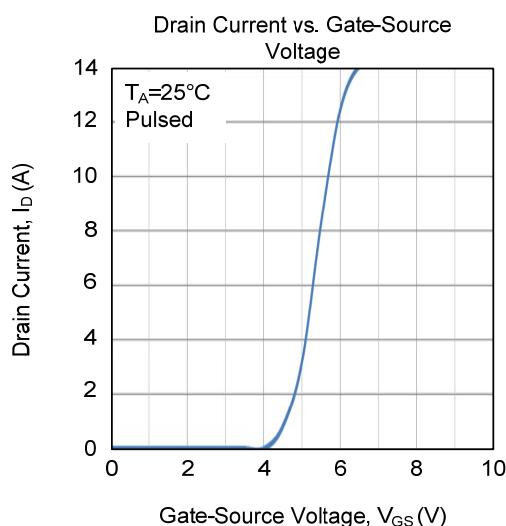
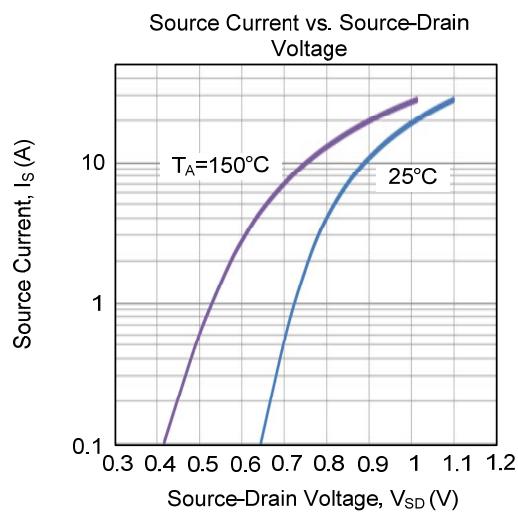
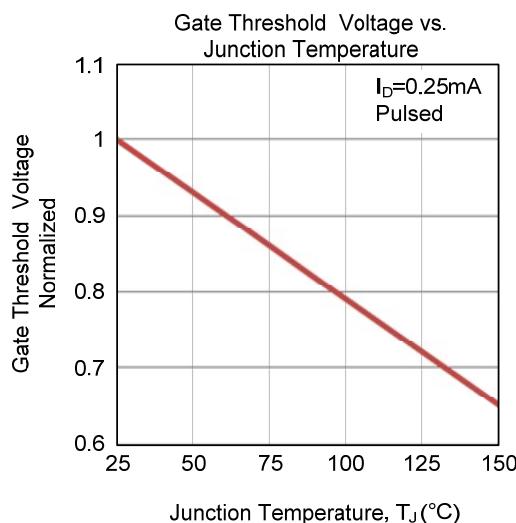
Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

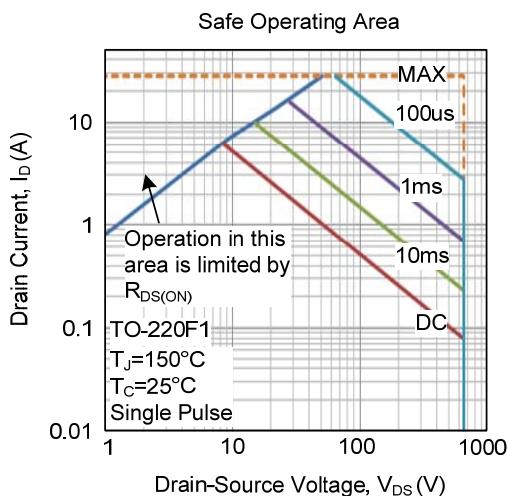
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.